

Unit
B1

complete their growth after forming grain boundaries 15.

Page 7, Paragraph beginning at line 9 of the substitute specification filed February 23, 2001:

B2

Figs. 1A to 1C are plan views illustrating a typical crystallization process of a polycrystalline silicon layer.

IN THE DRAWINGS

Applicant herewith submits a Request for Drawing Change to insert drawing 1B.

IN THE CLAIMS

Please **AMEND** claims 1 and 7 as follows (marked up version of the claim change is attached):

B3
Sub C1

1. (Amended) A method of forming a polycrystalline silicon layer, comprising:

forming an amorphous silicon layer on a substrate;

melting the amorphous silicon layer using a laser beam thereby forming the polycrystalline silicon layer by adopting a mask; and

melting an upper portion of the polycrystalline silicon layer using the laser beam by adopting the mask thereby recrystallizing the upper portion of the polycrystalline silicon layer,

wherein at least some of said melting of said upper portion of said polycrystalline silicon layer is performed as said amorphous silicon layer is melted.